

INJ0001AX SERIES

High speed switching
Silicon P-channel MOSFET

DESCRIPTION

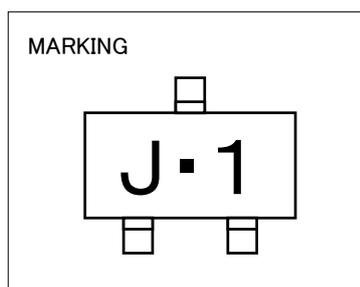
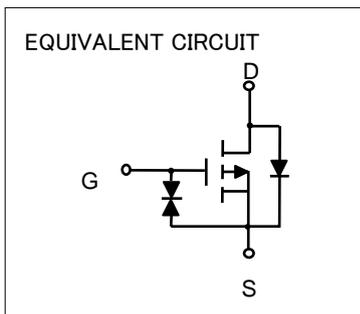
INJ0001AX is a Silicon P-channel MOSFET. This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

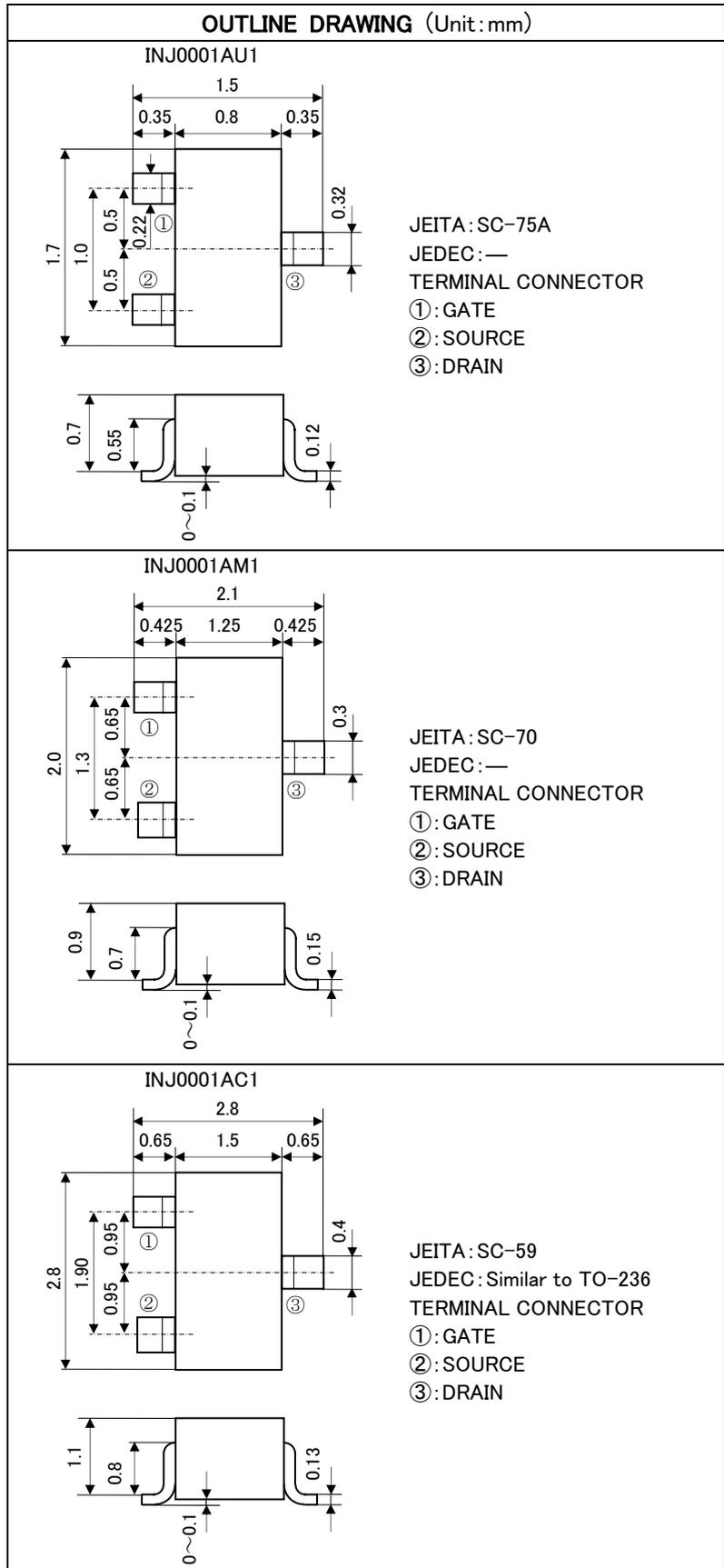
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage -2.5V
- Low on Resistance.
 $R_{DS(ON)} = 7\ \Omega$ (TYP) @ $I_D = -100\text{mA}$, $V_{GS} = -4.0\text{V}$
- High speed switching.
- Small package for easy mounting.

APPLICATION

High speed switching, Analog switching



OUTLINE DRAWING (Unit:mm)



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MAXIMUM RATING (Ta=25°C)

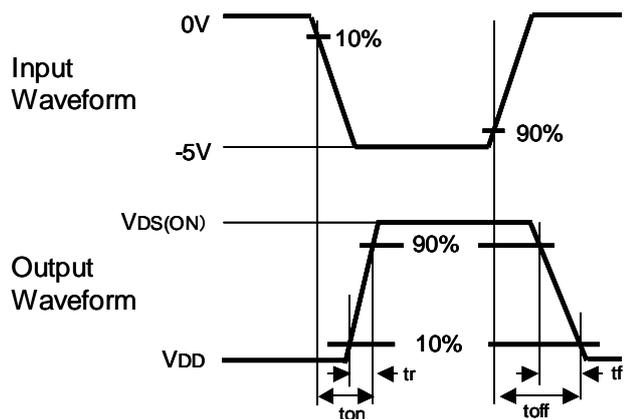
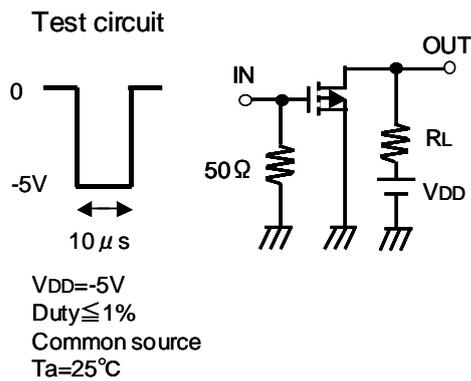
SYMBOL	PARAMETER	RATING			UNIT
		INJ0001AU1	INJ0001AM1	INJ0001AC1	
V _{DSS}	Drain-source voltage	-50			V
V _{GSS}	Gate-source voltage	±8			V
I _D	Drain current(DC)	-100			mA
I _{DP}	Drain current(Pulse)	-400(※1)			mA
P _D	Total power dissipation	150	200		mW
T _{ch}	Channel temperature	+150			°C
T _{stg}	Range of Storage temperature	-55~+150			°C

※1: Pw ≤ 10μs, Duty cycle ≤ 1%

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V(BR)DSS	Drain-source breakdown voltage	I _D =-100μA, V _{GS} =0V	-50	-	-	V
I _{GSS}	Gate-source leak current	V _{GS} =±5V, V _{DS} =0V	-	-	±0.5	μA
I _{DSS}	Zero gate voltage drain current	V _{DS} =-50V, V _{GS} =0V	-	-	-1.0	μA
V _{th}	Gate threshold voltage	I _D =-250μA, V _{DS} =V _{GS}	-0.6	-	-1.2	V
Y _{fs}	Forward transfer admittance	V _{DS} =-10V, I _D =-0.1A	-	220	-	mS
R _{DS(ON)}	Static drain-source on-state resistance	I _D =-100mA, V _{GS} =-4.0V	-	7.0	-	Ω
C _{iss}	Input capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	-	28	-	pF
C _{oss}	Output capacitance		-	5.2	-	
t _{on}	Switching time	V _{DD} =-5V, I _D =-10mA V _{GS} =0~-5V	-	13	-	ns
t _{off}			-	135	-	

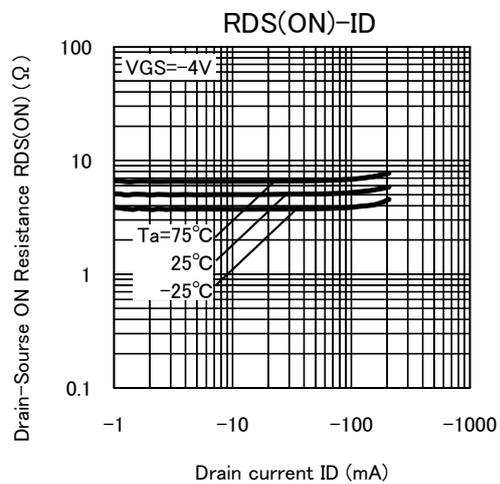
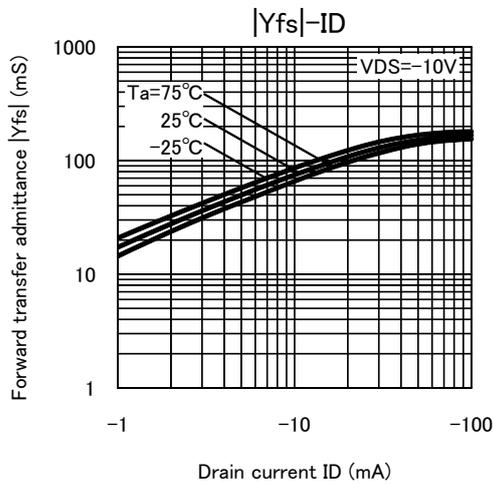
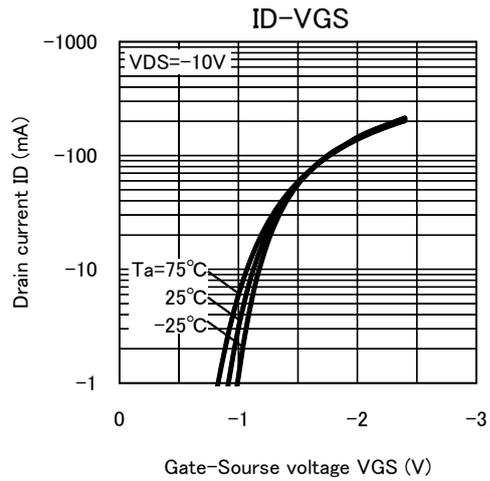
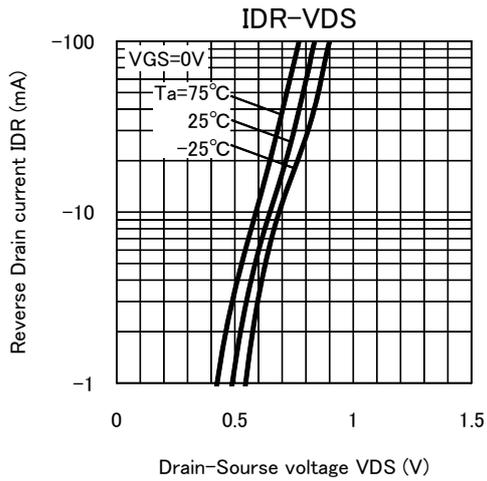
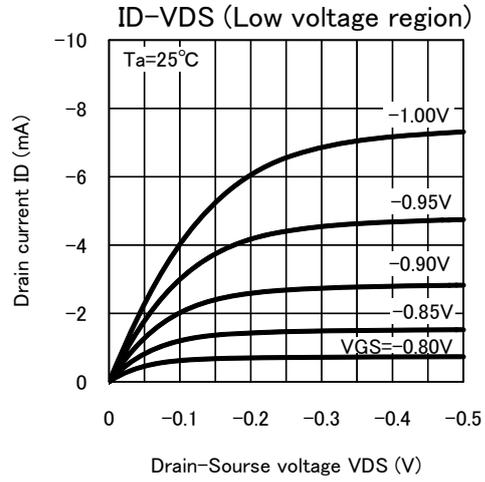
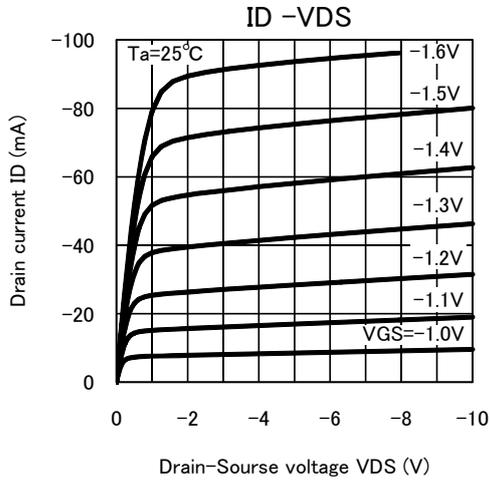
Switching time test condition



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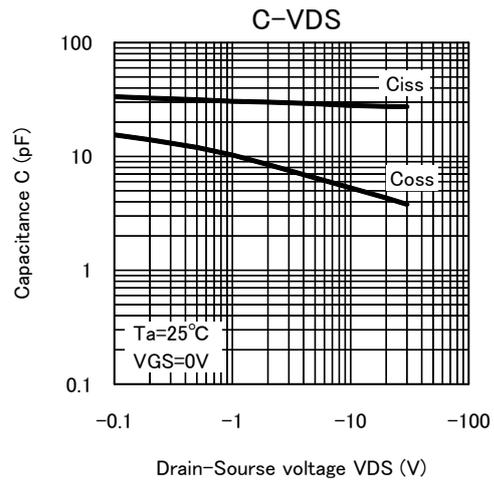
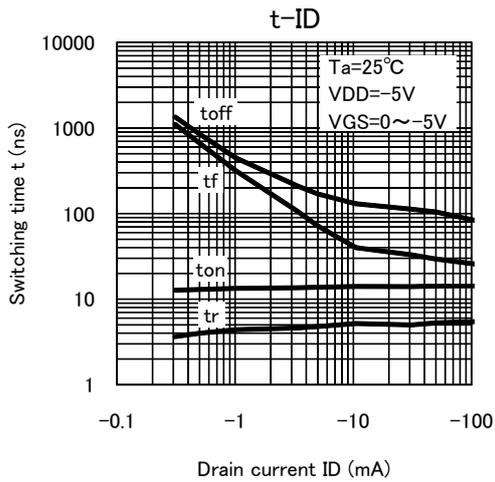
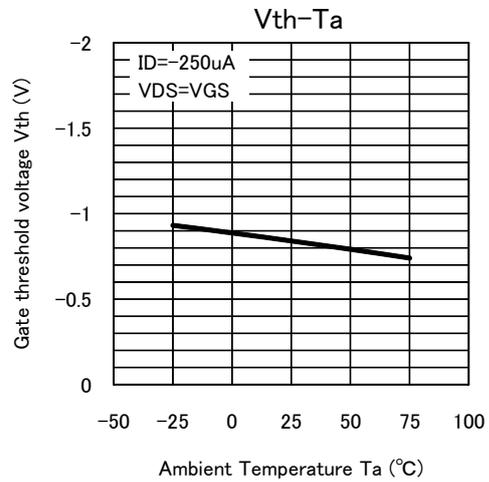
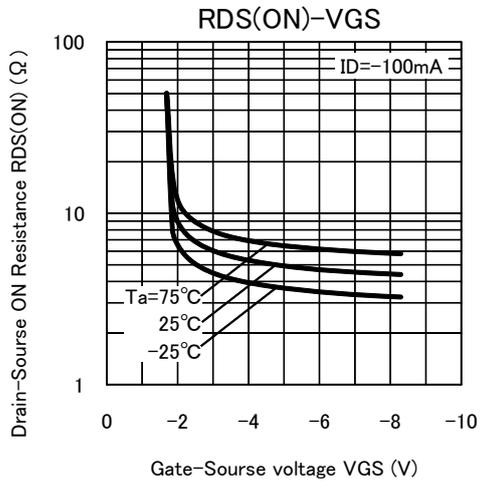
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TYPICAL CHARACTERISTICS



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